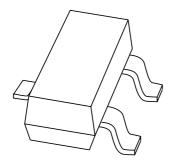
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT54 seriesSchottky barrier (double) diodes

Product specification Supersedes data of 2001 Oct 12 2002 Mar 04





Schottky barrier (double) diodes

BAT54 series

FEATURES

- Low forward voltage
- · Guard ring protected
- Small plastic SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- · Blocking diodes.

DESCRIPTION

Planar Schottky barrier diodes encapsulated in a SOT23 small plastic SMD package. Single diodes and double diodes with different pinning are available.

MARKING

TYPE NUMBER	MARKING CODE(1)
BAT54	L4*
BAT54A	L42 or *V3
BAT54C	L43 or *W1
BAT54S	L44 or *V4

Note

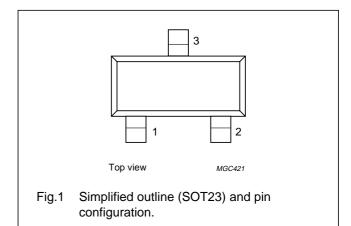
1. * = p: Made in Hong Kong.

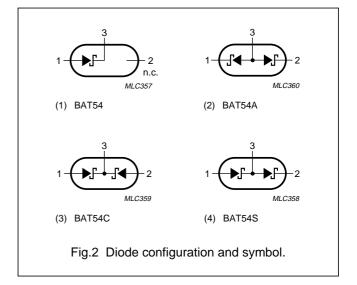
* = t : Made in Malaysia.

* = W: Made in China.

PINNING

PIN	DESCRIPTION							
FIN	BAT54	BAT54A BAT54C		BAT54S				
1	а	k ₁	a ₁	a ₁				
2	n.c.	k ₂	a ₂	k ₂				
3	k	a ₁ , a ₂	k ₁ , k ₂	k ₁ , a ₂				





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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode		·	·	•	
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		_	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	_	300	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms	_	600	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	230	mW

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	500	K/W
'	ambient			

Note

1. Refer to SOT23 standard mounting conditions.

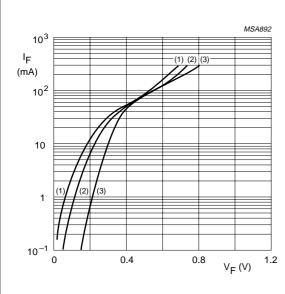
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode		•	•	
V _F	forward voltage	see Fig.3		
		$I_F = 0.1 \text{ mA}$	240	mV
		I _F = 1 mA	320	mV
		I _F = 10 mA	400	mV
		I _F = 30 mA	500	mV
		I _F = 100 mA	800	mV
I _R	reverse current	V _R = 25 V; see Fig.4	2	μΑ
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.6	5	ns
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; see Fig.5	10	pF

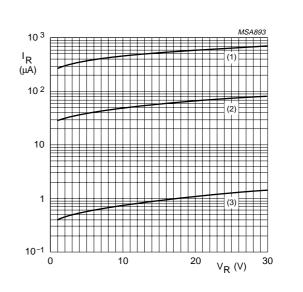
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- (1) $T_{amb} = 125 \,^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

Fig.4 Reverse current as a function of reverse voltage; typical values.

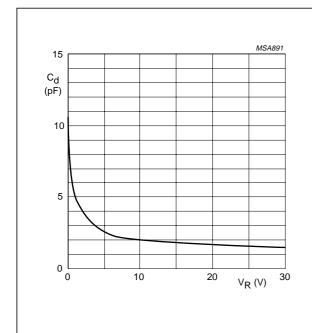
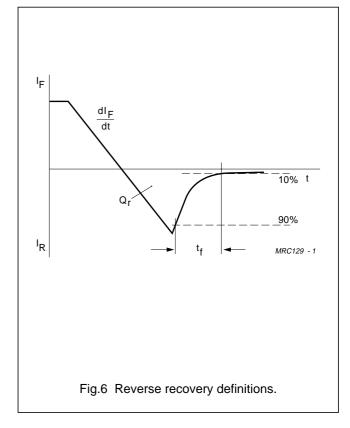


Fig.5 Diode capacitance as a function of reverse voltage; typical values.

f = 1 MHz; $T_{amb} = 25 \,^{\circ}\text{C}$.



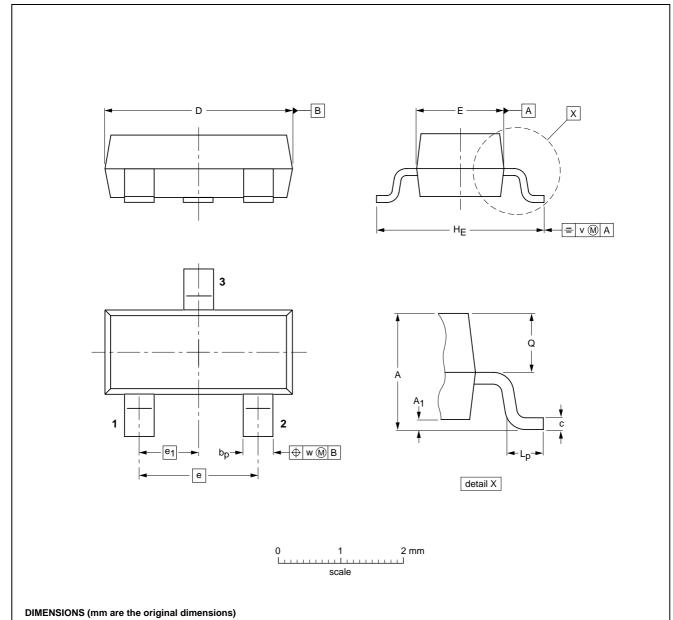
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



	Αı		П

UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-97-02-28- 99-09-13

2002 Mar 04 5

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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NOTES

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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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